Ion Implantation and Activation

About the ebook

This e-book series presents the derivation process of related models in a comprehensive step by step manner. This volume describes the diffusion phenomenon under the thermal equilibrium on point defect concentration and the features of transient enhanced diffusion (TED). The volume also presents methods for the oxidation and redistribution of impurities in polycrystalline silicon for extraction as well as some analytical models related to the VLSI process.

Contents

Diffusion Under Thermal Equilibrium
Paring Diffusion Equation
Experimental Data Associated with Transient Diffusion
Simple Treatment of Transient Enhanced Diffusion
Thermal Oxidation
Segregation
Analytical Diffusion Profiles Under Various Boundary Conditions

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